

#### General Description

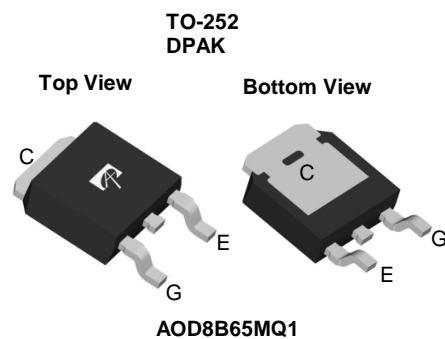
- Latest AlphaIGBT (αIGBT) technology
- 650V breakdown voltage
- IGBT copacked with very fast and soft antiparallel diode
- Very good EMI performance with lower turn-on switching losses
- High short-circuit ruggedness

#### Applications

- Motor drives
- Home appliance applications
- Other hard switching applications

#### Product Summary

|  |      |
|--|------|
| $V_{CE}$                                 | 650V |
| $I_C$ ( $T_C=100^\circ\text{C}$ )        | 8A   |
| $V_{CE(sat)}$ ( $T_J=25^\circ\text{C}$ ) | 1.8V |



| Orderable Part Number | Package Type | Form        | Minimum Order Quantity |
|-----------------------|--------------|-------------|------------------------|
| AOD8B65MQ1            | TO252        | Tape & Reel | 2500                   |

#### Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

| Parameter  | Symbol         | AOD8B65MQ1              | Units            |
|--|----------------|-------------------------|------------------|
| Collector-Emitter Voltage  | $V_{CE}$       | 650                     | V                |
| Gate-Emitter Voltage   | $V_{GE}$       | $\pm 30$                | V                |
| Continuous Collector Current   | $I_C$          | $T_C=25^\circ\text{C}$  | 16               |
|  |                | $T_C=100^\circ\text{C}$ | 8                |
| Pulsed Collector Current, Limited by $T_{Jmax}$  | $I_{CM}$       | 24                      | A                |
| Turn-Off SOA, $V_{CE} \leq 650\text{V}$ , Limited by $T_{Jmax}$  | $I_{LM}$       | 24                      | A                |
| Continuous Diode Forward Current   | $I_F$          | $T_C=25^\circ\text{C}$  | 16               |
|  |                | $T_C=100^\circ\text{C}$ | 8                |
| Diode Pulsed Current, Limited by $T_{Jmax}$  | $I_{FM}$       | 24                      | A                |
| Short Circuit Withstanding Time <sup>(1)</sup><br>$V_{GE}=15\text{V}$ , $V_{CC} \leq 400\text{V}$ , $T_J \leq 150^\circ\text{C}$ | $t_{SC}$       | 5                       | $\mu\text{s}$    |
| Power Dissipation  | $P_D$          | $T_C=25^\circ\text{C}$  | 89               |
|  |                | $T_C=100^\circ\text{C}$ | 36               |
| Junction and Storage Temperature Range   | $T_J, T_{STG}$ | -55 to 150              | $^\circ\text{C}$ |
| Maximum Lead Temperature for Soldering Purpose, 1/8" from case for 5 seconds   | $T_L$          | 300                     | $^\circ\text{C}$ |

#### Thermal Characteristics

| Parameter                      | Symbol          | AOD8B65MQ1 | Units              |
|--------------------------------|-----------------|------------|--------------------|
| Maximum Junction-to-Ambient    | $R_{\theta JA}$ | 55         | $^\circ\text{C/W}$ |
| Maximum IGBT Junction-to-Case  | $R_{\theta JC}$ | 1.4        | $^\circ\text{C/W}$ |
| Maximum Diode Junction-to-Case | $R_{\theta JC}$ | 3          | $^\circ\text{C/W}$ |

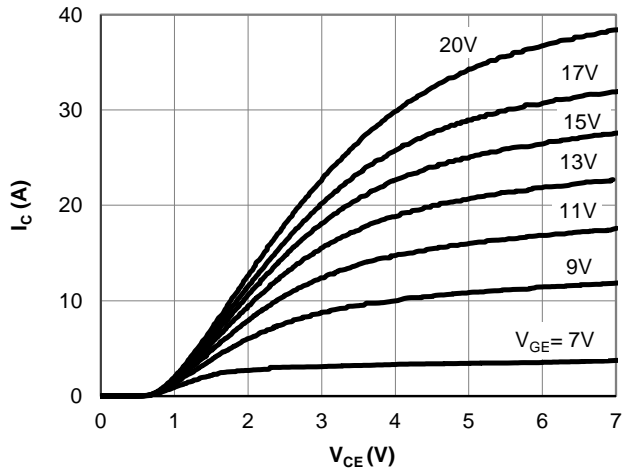
(1) Allowed number of short circuits: <1000; time between short circuits: >1s.

**Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)**

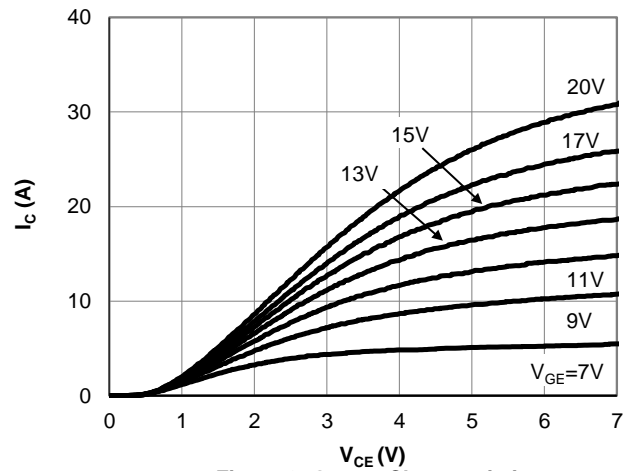
| Symbol   | Parameter                            | Conditions   | Min                   | Typ  | Max  | Units |    |
|--|--------------------------------------|--|-----------------------|------|------|-------|----|
| <b>STATIC PARAMETERS</b>   |                                      |  |                       |      |      |       |    |
| BV <sub>CE(S)</sub>  | Collector-Emitter Breakdown Voltage  | I <sub>C</sub> =1mA, V <sub>GE</sub> =0V, T <sub>J</sub> =25°C   | 650                   | -    | -    | V     |    |
| V <sub>CE(sat)</sub>   | Collector-Emitter Saturation Voltage | V <sub>GE</sub> =15V, I <sub>C</sub> =8A   | T <sub>J</sub> =25°C  | -    | 1.8  | 2.25  | V  |
|  |                                      |  | T <sub>J</sub> =125°C | -    | 2.09 | -     |    |
|  |                                      |  | T <sub>J</sub> =150°C | -    | 2.19 | -     |    |
| V <sub>F</sub>   | Diode Forward Voltage                | V <sub>GE</sub> =0V, I <sub>F</sub> =8A  | T <sub>J</sub> =25°C  | -    | 1.52 | 1.9   | V  |
|  |                                      |  | T <sub>J</sub> =125°C | -    | 1.59 | -     |    |
|  |                                      |  | T <sub>J</sub> =150°C | -    | 1.56 | -     |    |
| V <sub>GE(th)</sub>  | Gate-Emitter Threshold Voltage       | V <sub>CE</sub> =5V, I <sub>C</sub> =1mA   | -                     | 4.9  | -    | V     |    |
| I <sub>CE(S)</sub>   | Zero Gate Voltage Collector Current  | V <sub>CE</sub> =650V, V <sub>GE</sub> =0V   | T <sub>J</sub> =25°C  | -    | -    | 10    | μA |
|  |                                      |  | T <sub>J</sub> =125°C | -    | -    | 500   |    |
|  |                                      |  | T <sub>J</sub> =150°C | -    | -    | 1000  |    |
| I <sub>GES</sub>   | Gate-Emitter Leakage Current         | V <sub>CE</sub> =0V, V <sub>GE</sub> =±30V   | -                     | -    | ±100 | nA    |    |
| g <sub>FS</sub>  | Forward Transconductance             | V <sub>CE</sub> =20V, I <sub>C</sub> =8A   | -                     | 5    | -    | S     |    |
| <b>DYNAMIC PARAMETERS</b>  |                                      |  |                       |      |      |       |    |
| C <sub>ies</sub>   | Input Capacitance                    | V <sub>GE</sub> =0V, V <sub>CC</sub> =25V, f=1MHz  | -                     | 500  | -    | pF    |    |
| C <sub>oes</sub>   | Output Capacitance                   |  | -                     | 45   | -    | pF    |    |
| C <sub>res</sub>   | Reverse Transfer Capacitance         |  | -                     | 16   | -    | pF    |    |
| Q <sub>g</sub>   | Total Gate Charge                    | V <sub>GE</sub> =15V, V <sub>CC</sub> =520V, I <sub>C</sub> =8A  | -                     | 22   | -    | nC    |    |
| Q <sub>ge</sub>  | Gate to Emitter Charge               |  | -                     | 6.5  | -    | nC    |    |
| Q <sub>gc</sub>  | Gate to Collector Charge             |  | -                     | 10   | -    | nC    |    |
| I <sub>C(SC)</sub>   | Short Circuit Collector Current      | V <sub>GE</sub> =15V, V <sub>CC</sub> =400V,<br>t <sub>sc</sub> ≤5us, T <sub>J</sub> ≤150°C                        | -                     | 50   | -    | A     |    |
| R <sub>g</sub>   | Gate Resistance                      | V <sub>GE</sub> =0V, V <sub>CC</sub> =0V, f=1MHz   | -                     | 7    | -    | Ω     |    |
| <b>SWITCHING PARAMETERS, (Load Inductive, T<sub>J</sub>=25°C)</b>  |                                      |  |                       |      |      |       |    |
| t <sub>D(on)</sub>   | Turn-On Delay Time                   | T <sub>J</sub> =25°C<br>V <sub>GE</sub> =15V, V <sub>CC</sub> =400V, I <sub>C</sub> =8A,<br>R <sub>G</sub> =37.5Ω  | -                     | 8.5  | -    | ns    |    |
| t <sub>r</sub>   | Turn-On Rise Time                    |  | -                     | 14   | -    | ns    |    |
| t <sub>D(off)</sub>  | Turn-Off Delay Time                  |  | -                     | 102  | -    | ns    |    |
| t <sub>f</sub>   | Turn-Off Fall Time                   |  | -                     | 16   | -    | ns    |    |
| E <sub>on</sub>  | Turn-On Energy                       |  | -                     | 0.16 | -    | mJ    |    |
| E <sub>off</sub>   | Turn-Off Energy                      |  | -                     | 0.11 | -    | mJ    |    |
| E <sub>total</sub>   | Total Switching Energy               |  | -                     | 0.27 | -    | mJ    |    |
| t <sub>rr</sub>  | Diode Reverse Recovery Time          | T <sub>J</sub> =25°C<br>I <sub>F</sub> =8A, di/dt=200A/μs, V <sub>CC</sub> =400V                                   | -                     | 94   | -    | ns    |    |
| Q <sub>rr</sub>  | Diode Reverse Recovery Charge        |  | -                     | 0.2  | -    | μC    |    |
| I <sub>rm</sub>  | Diode Peak Reverse Recovery Current  |  | -                     | 3.49 | -    | A     |    |
| <b>SWITCHING PARAMETERS, (Load Inductive, T<sub>J</sub>=150°C)</b> |                                      |  |                       |      |      |       |    |
| t <sub>D(on)</sub>   | Turn-On Delay Time                   | T <sub>J</sub> =150°C<br>V <sub>GE</sub> =15V, V <sub>CC</sub> =400V, I <sub>C</sub> =8A,<br>R <sub>G</sub> =37.5Ω | -                     | 7.5  | -    | ns    |    |
| t <sub>r</sub>   | Turn-On Rise Time                    |  | -                     | 15   | -    | ns    |    |
| t <sub>D(off)</sub>  | Turn-Off Delay Time                  |  | -                     | 122  | -    | ns    |    |
| t <sub>f</sub>   | Turn-Off Fall Time                   |  | -                     | 26   | -    | ns    |    |
| E <sub>on</sub>  | Turn-On Energy                       |  | -                     | 0.19 | -    | mJ    |    |
| E <sub>off</sub>   | Turn-Off Energy                      |  | -                     | 0.18 | -    | mJ    |    |
| E <sub>total</sub>   | Total Switching Energy               |  | -                     | 0.37 | -    | mJ    |    |
| t <sub>rr</sub>  | Diode Reverse Recovery Time          | T <sub>J</sub> =150°C<br>I <sub>F</sub> =8A, di/dt=200A/μs, V <sub>CC</sub> =400V                                  | -                     | 133  | -    | ns    |    |
| Q <sub>rr</sub>  | Diode Reverse Recovery Charge        |  | -                     | 0.38 | -    | μC    |    |
| I <sub>rm</sub>  | Diode Peak Reverse Recovery Current  |  | -                     | 4.39 | -    | A     |    |

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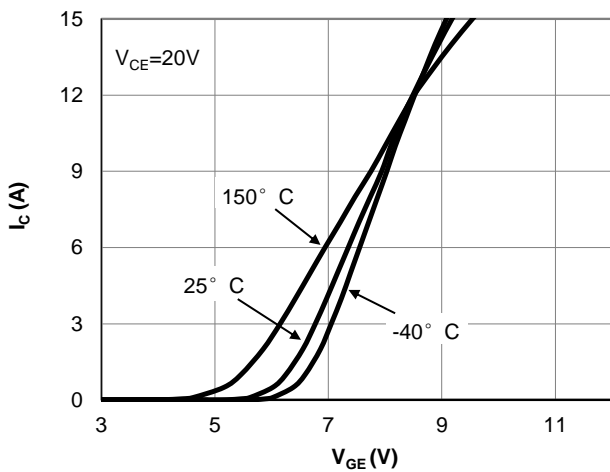
**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**



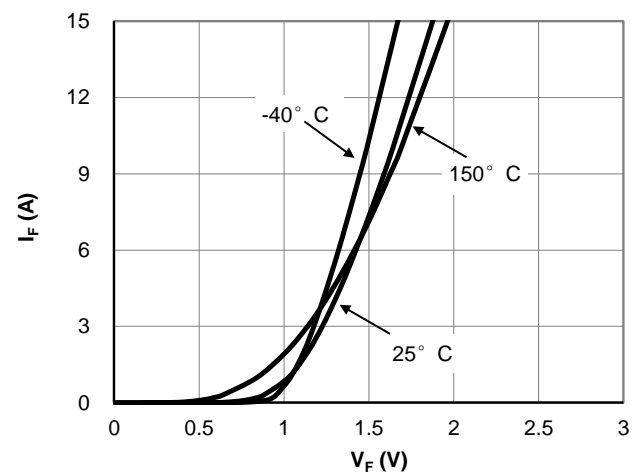
**Figure 1: Output Characteristic**  
( $T_j=25^\circ\text{C}$ )



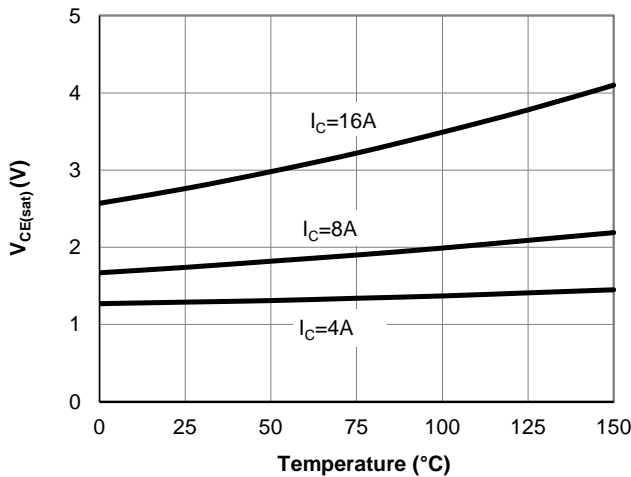
**Figure 2: Output Characteristic**  
( $T_j=150^\circ\text{C}$ )



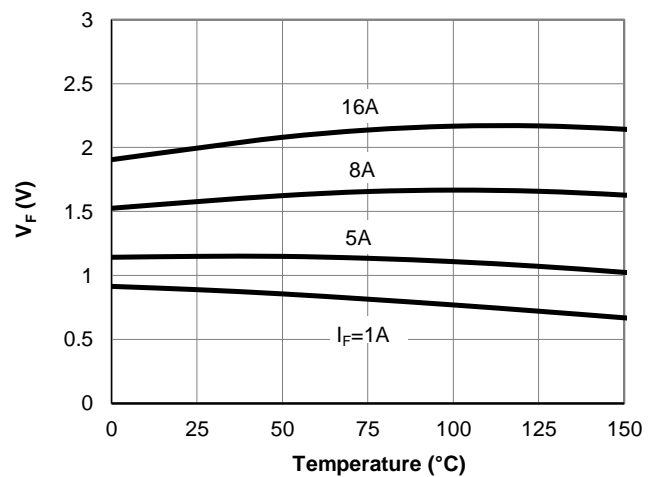
**Figure 3: Transfer Characteristic**



**Figure 4: Diode Characteristic**



**Figure 5: Collector-Emitter Saturation Voltage vs. Junction Temperature**



**Figure 6: Diode Forward voltage vs. Junction Temperature**

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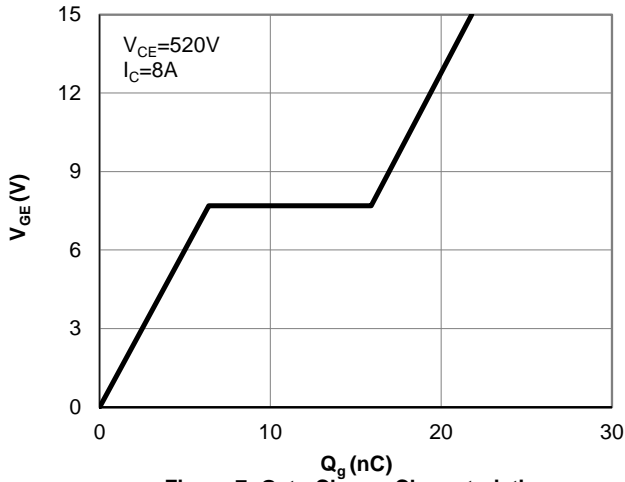


Figure 7: Gate-Charge Characteristics

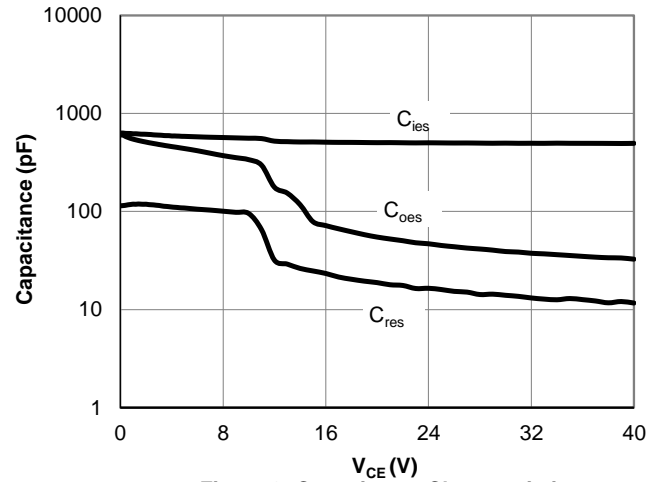


Figure 8: Capacitance Characteristic

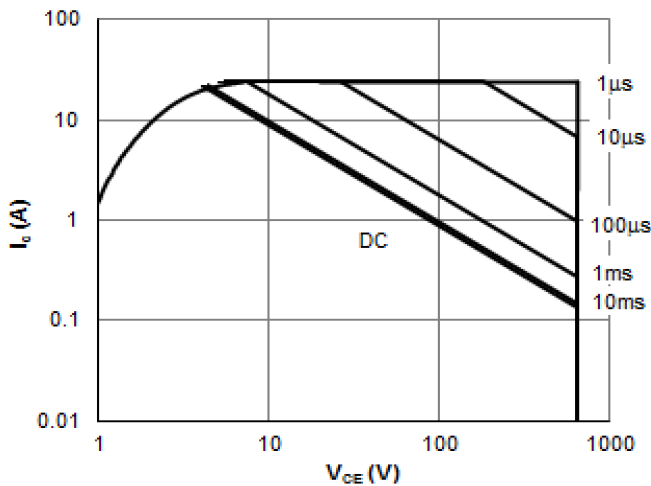


Figure 9: Forward Bias Safe Operating Area  
( $T_C=25^\circ\text{C}$ ,  $V_{GE}=15\text{V}$ )

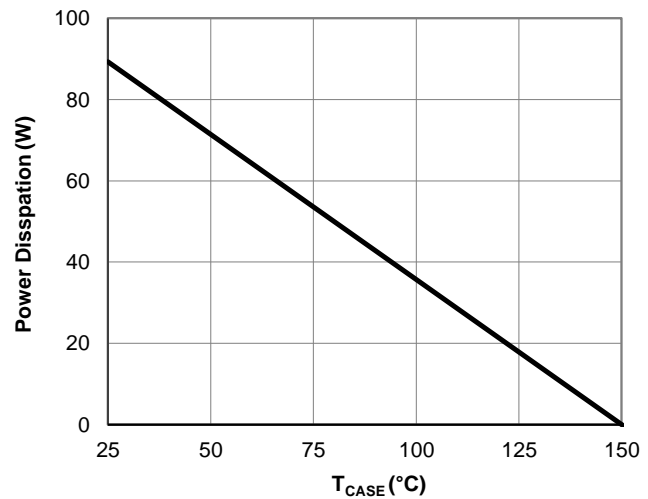


Figure 10: Power Dissipation as a Function of Case

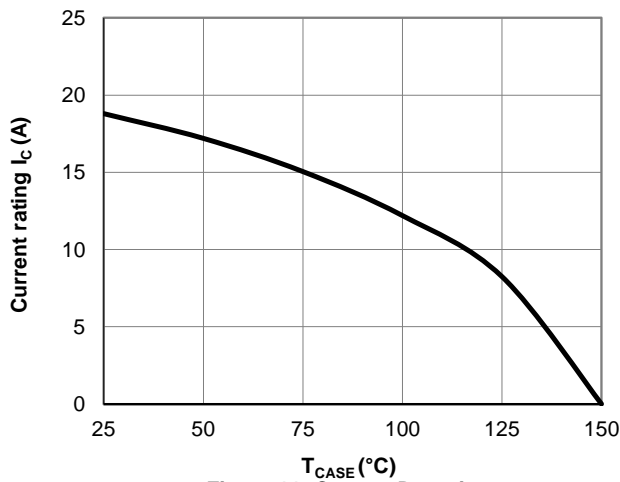


Figure 11: Current De-rating

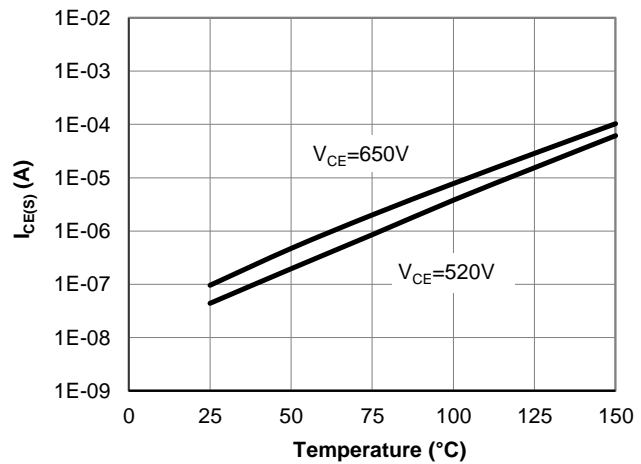
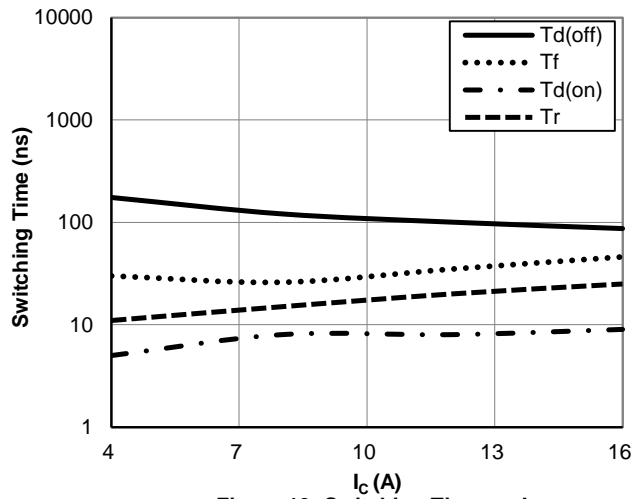
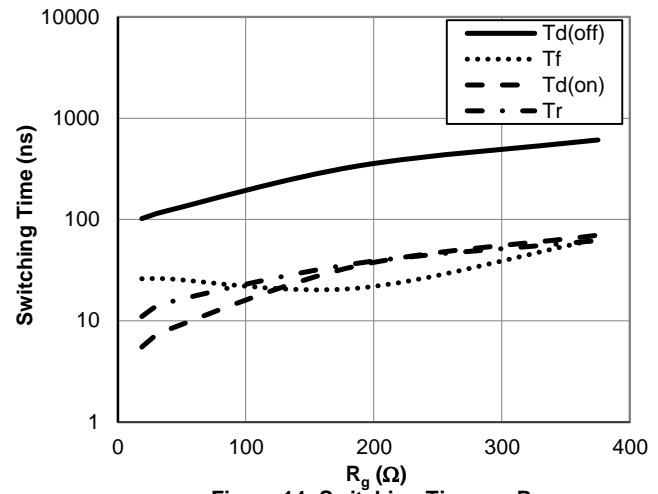


Figure 12: Diode Reverse Leakage Current vs. Junction Temperature

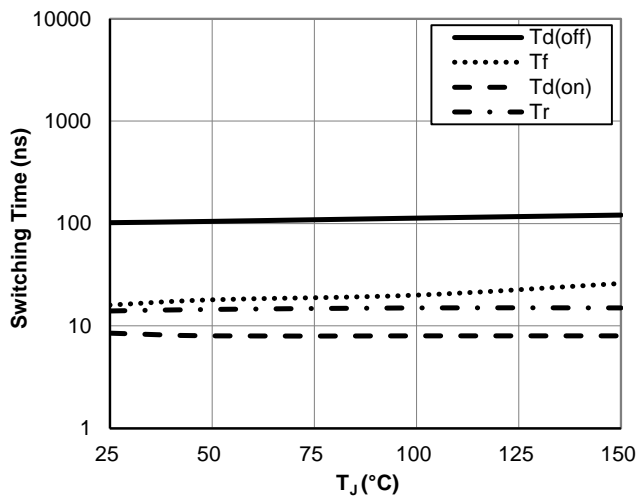
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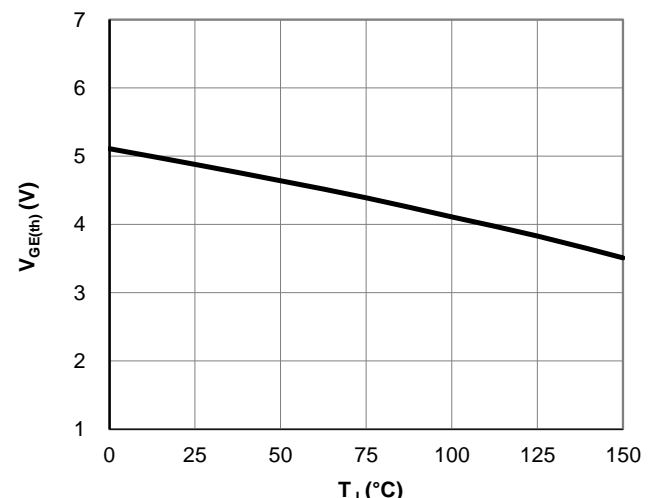
**Figure 13: Switching Time vs.  $I_C$**   
( $T_J=150^\circ\text{C}$ ,  $V_{GE}=15\text{V}$ ,  $V_{CE}=400\text{V}$ ,  $R_g=37.5\Omega$ )



**Figure 14: Switching Time vs.  $R_g$**   
( $T_J=150^\circ\text{C}$ ,  $V_{GE}=15\text{V}$ ,  $V_{CE}=400\text{V}$ ,  $I_C=8\text{A}$ )

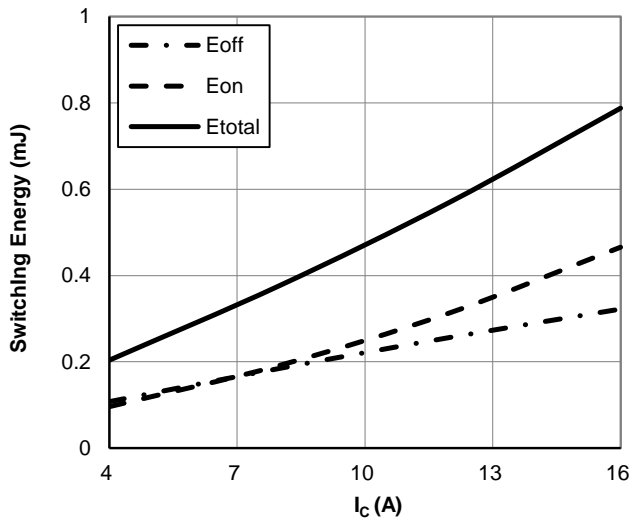


**Figure 15: Switching Time vs.  $T_J$**   
( $V_{GE}=15\text{V}$ ,  $V_{CE}=400\text{V}$ ,  $I_C=8\text{A}$ ,  $R_g=37.5\Omega$ )

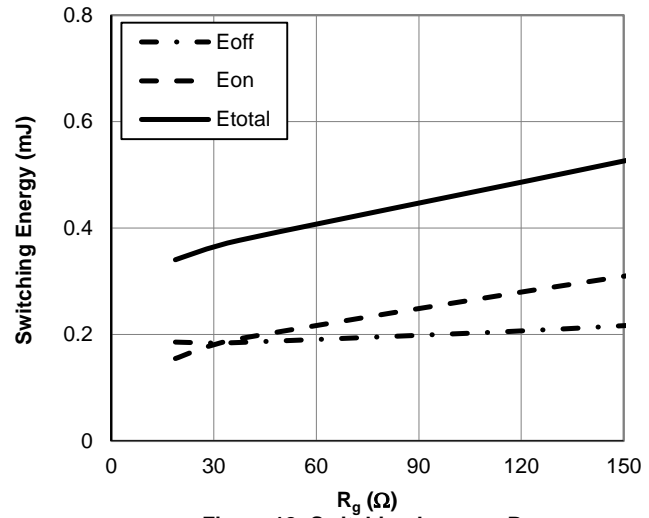


**Figure 16:  $V_{GE(th)}$  vs.  $T_J$**

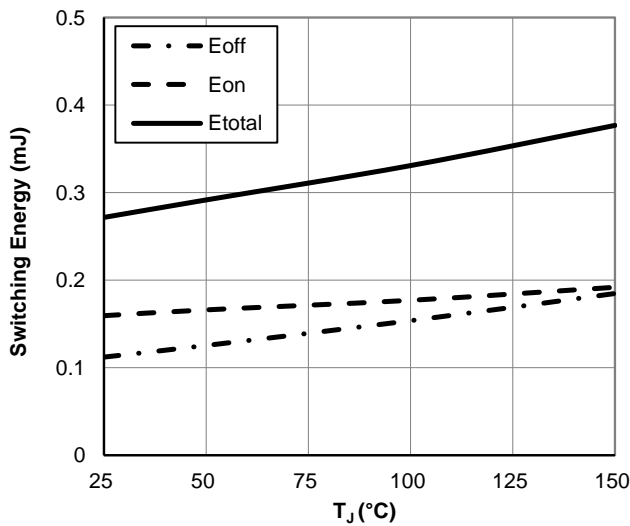
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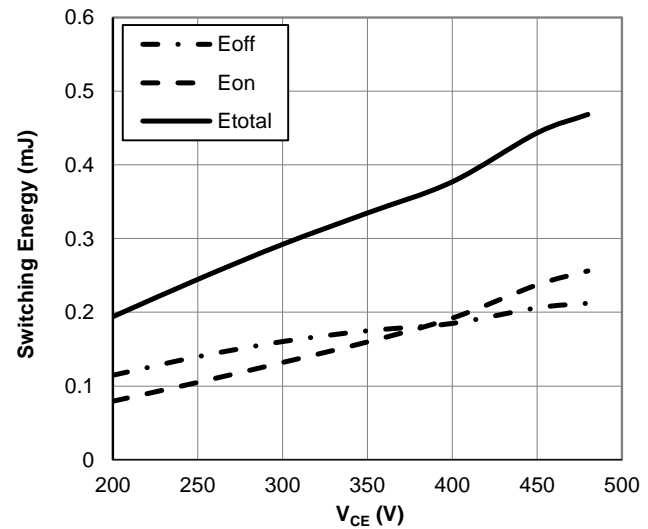
**Figure 17: Switching Loss vs.  $I_C$**   
( $T_J=150^\circ\text{C}$ ,  $V_{GE}=15\text{V}$ ,  $V_{CE}=400\text{V}$ ,  $R_g=37.5\Omega$ )



**Figure 18: Switching Loss vs.  $R_g$**   
( $T_J=150^\circ\text{C}$ ,  $V_{GE}=15\text{V}$ ,  $V_{CE}=400\text{V}$ ,  $I_C=8\text{A}$ )

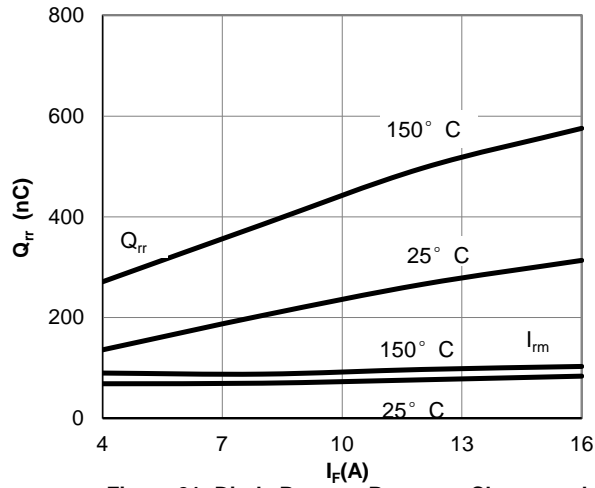


**Figure 19: Switching Loss vs.  $T_J$**   
( $V_{GE}=15\text{V}$ ,  $V_{CE}=400\text{V}$ ,  $I_C=8\text{A}$ ,  $R_g=37.5\Omega$ )

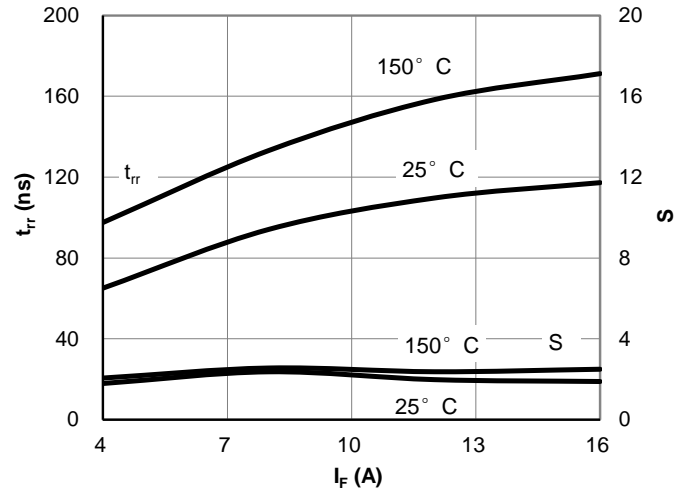


**Figure 20: Switching Loss vs.  $V_{CE}$**   
( $T_J=150^\circ\text{C}$ ,  $V_{GE}=15\text{V}$ ,  $I_C=8\text{A}$ ,  $R_g=37.5\Omega$ )

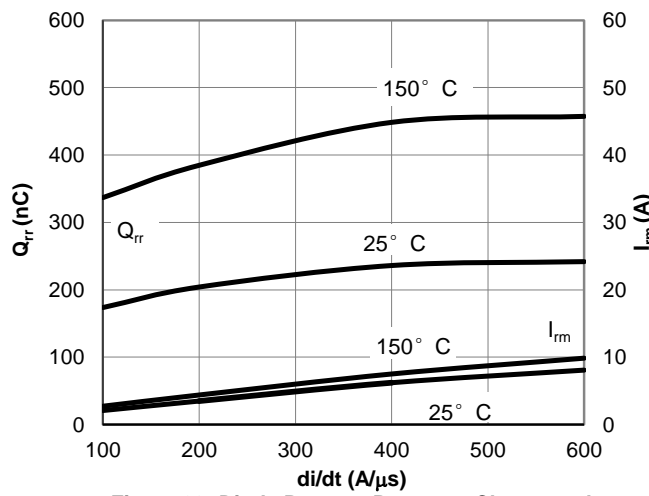
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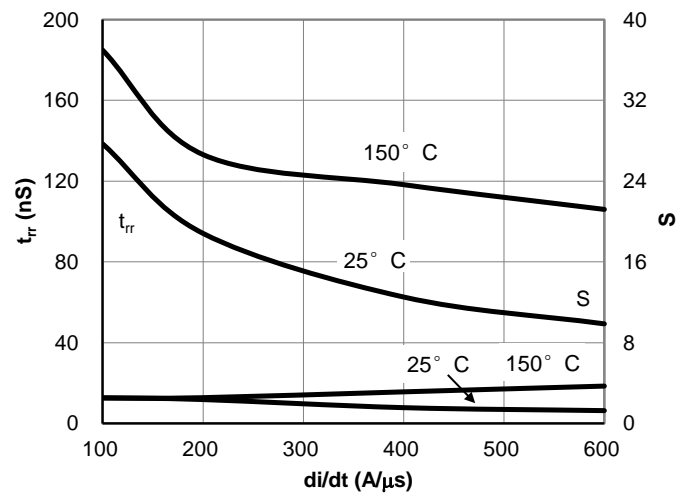
**Figure 21: Diode Reverse Recovery Charge and Peak Current vs. Conduction Current**  
( $V_{GE}=15V, V_{CE}=400V, di/dt=200A/\mu s$ )



**Figure 22: Diode Reverse Recovery Time and Softness Factor vs. Conduction Current**  
( $V_{GE}=15V, V_{CE}=400V, di/dt=200A/\mu s$ )

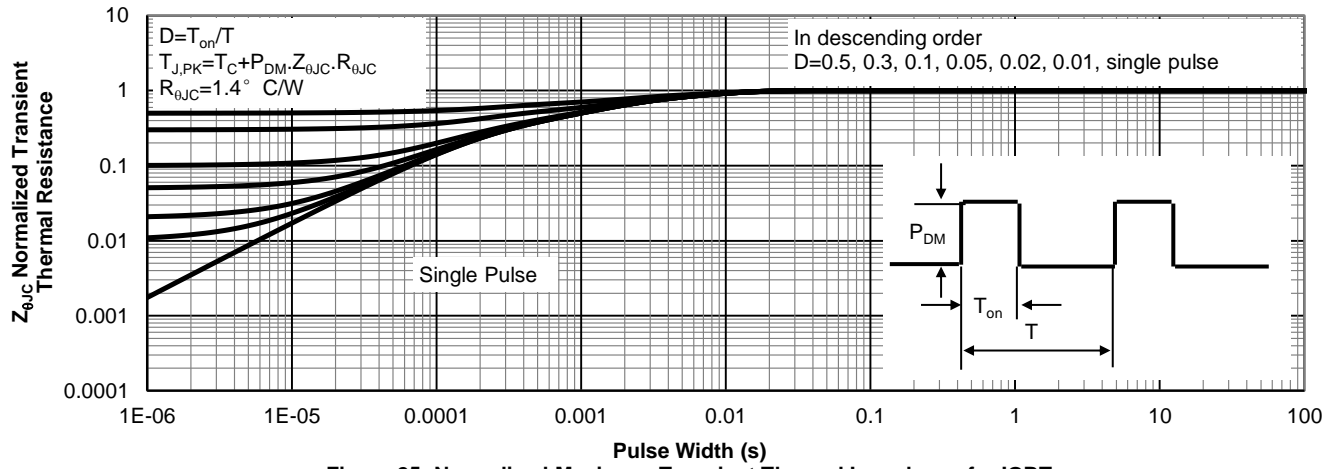


**Figure 23: Diode Reverse Recovery Charge and Peak Current vs. di/dt**  
( $V_{GE}=15V, V_{CE}=400V, I_F=8A$ )

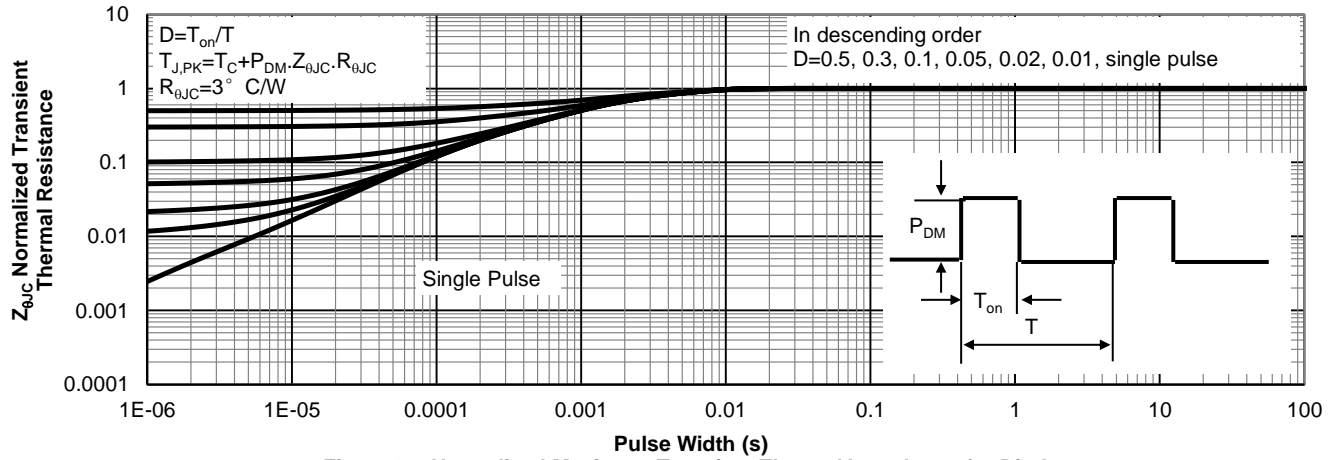


**Figure 24: Diode Reverse Recovery Time and Softness Factor vs. di/dt**  
( $V_{GE}=15V, V_{CE}=400V, I_F=8A$ )

**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**



**Figure 25: Normalized Maximum Transient Thermal Impedance for IGBT**



**Figure 26: Normalized Maximum Transient Thermal Impedance for Diode**



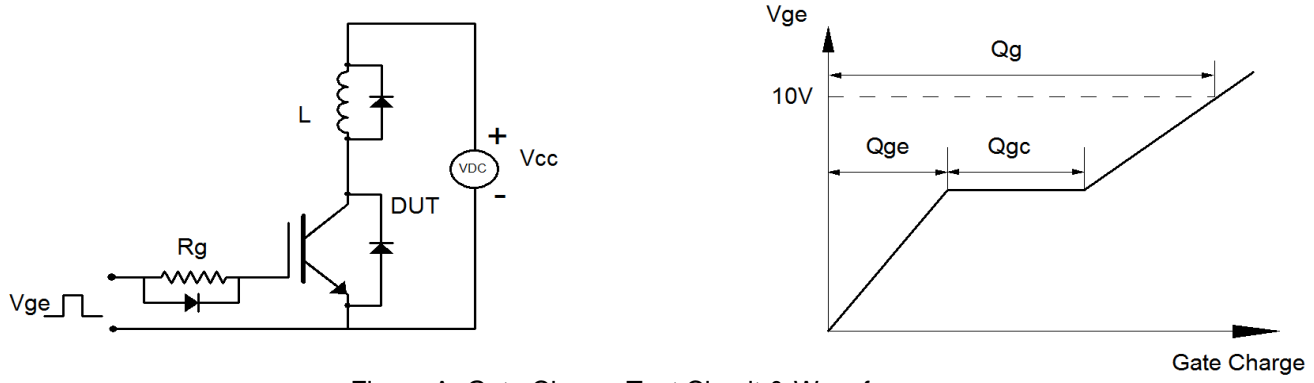


Figure A: Gate Charge Test Circuit & Waveforms

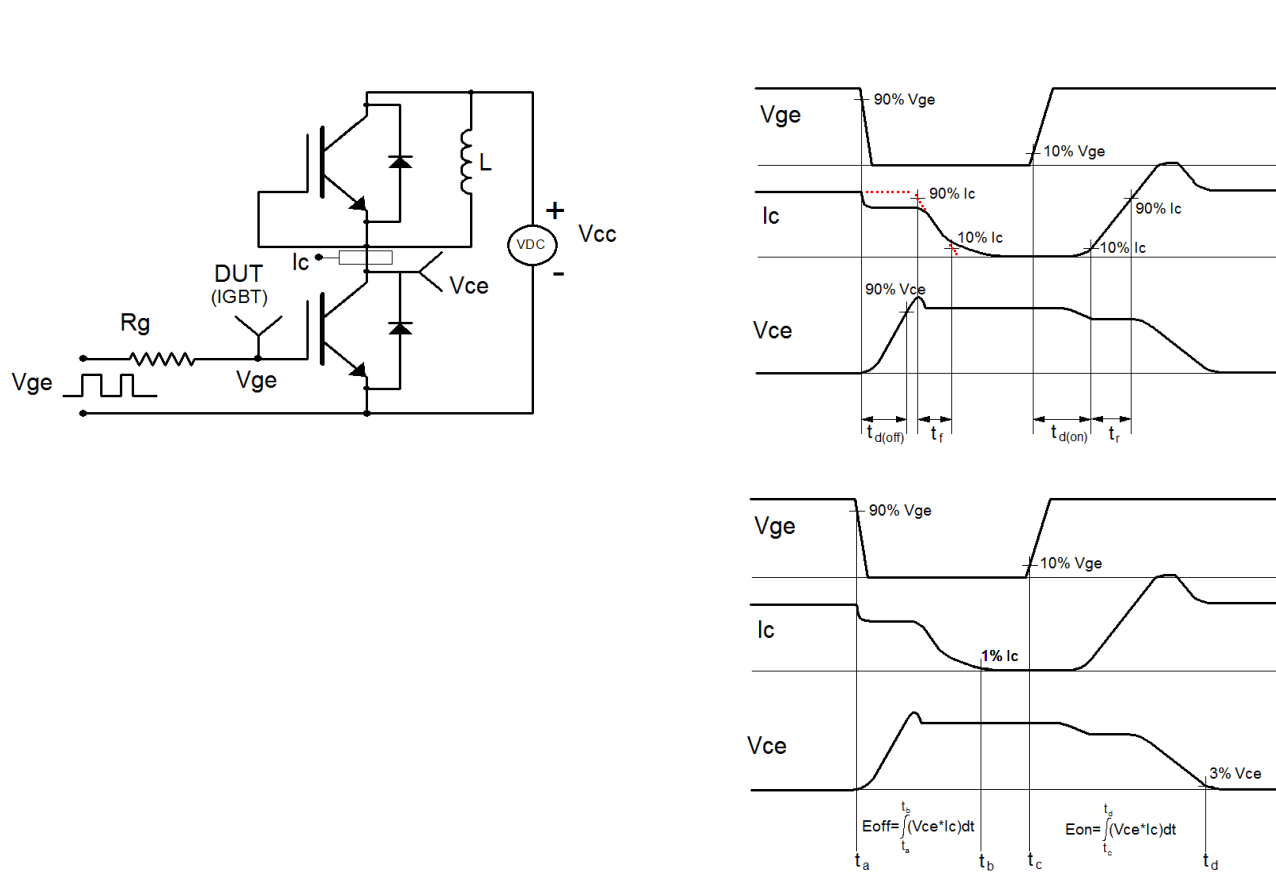


Figure B: Inductive Switching Test Circuit & Waveforms

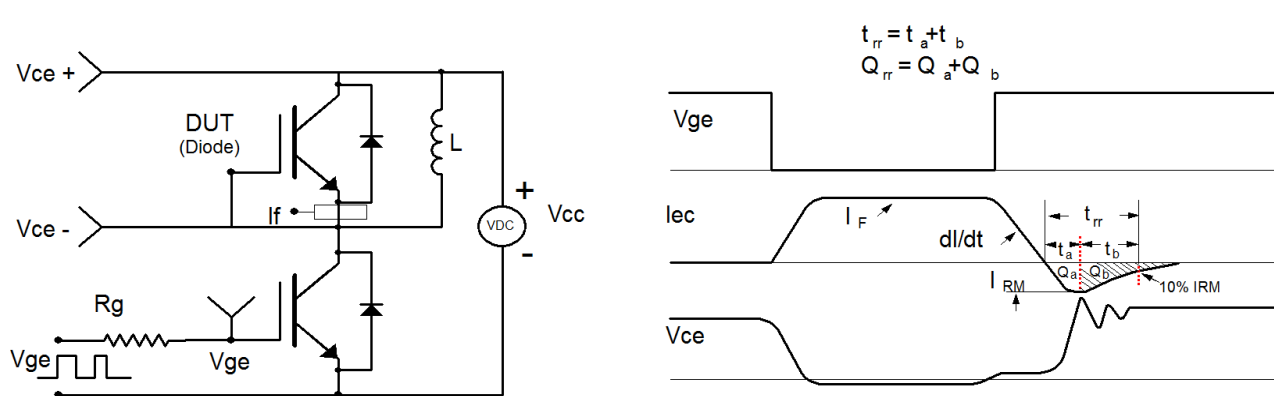


Figure C: Diode Recovery Test Circuit & Waveforms